

Description

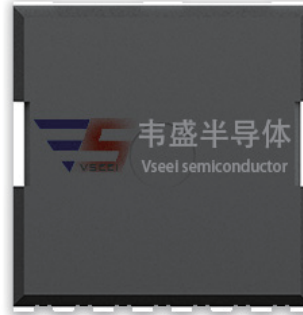
The VST06N010 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

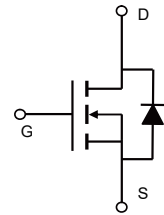
- $V_{DS} = 60V, I_D = 300A$
 $R_{DS(ON)} = 1.2m\Omega$ (typical) @ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



TOLL



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST06N010	VST06N010-OL	TOLL	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous (Silicon Limited)	I_D	300	A
Drain Current-Continuous ($T_C = 100^\circ C$)	$I_D (100^\circ C)$	225	A
Pulsed Drain Current	I_{DM}	1200	A
Maximum Power Dissipation	P_D	350	W
Derating factor		2.33	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	E_{AS}	2000	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	0.43	$^\circ C/W$
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Electrical Characteristics ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	60		-	V

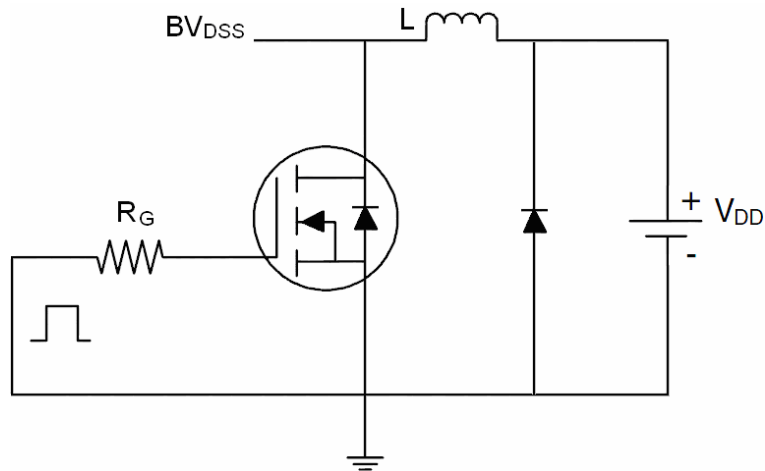
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.2	2.7	3.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =150A	-	1.2	1.5	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =150A	-	60	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, F=1.0MHz	-	8600	-	PF
Output Capacitance	C _{oss}		-	1800	-	PF
Reverse Transfer Capacitance	C _{rss}		-	54	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =150A V _{GS} =10V, R _G =4.7Ω	-	19	-	nS
Turn-on Rise Time	t _r		-	31	-	nS
Turn-Off Delay Time	t _{d(off)}		-	58	-	nS
Turn-Off Fall Time	t _f		-	23	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =150A, V _{GS} =10V	-	129		nC
Gate-Source Charge	Q _{gs}		-	40.6		nC
Gate-Drain Charge	Q _{gd}		-	23.9		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =300A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	300	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =150A	-	67		nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs(Note3)	-	112		nC

Notes:

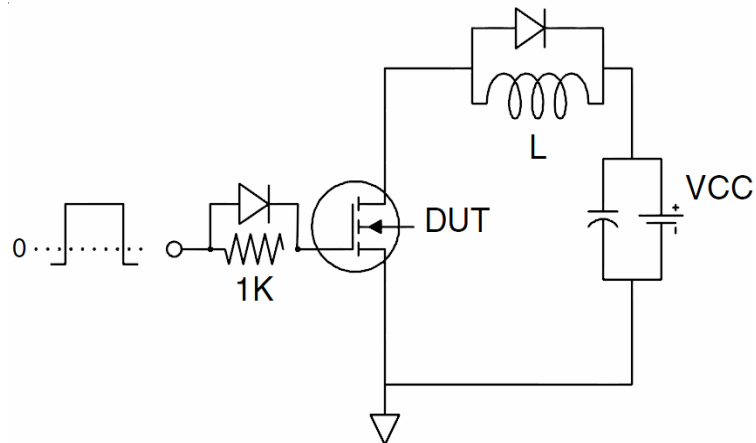
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^\circ C, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$

Test Circuit

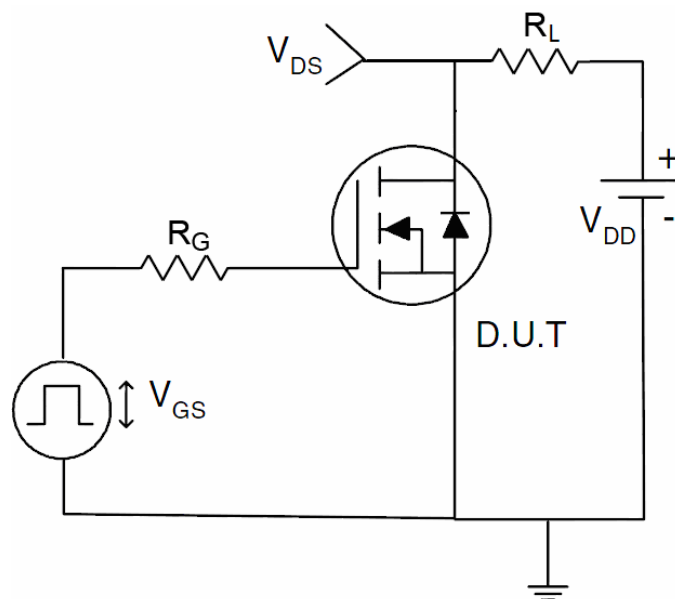
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

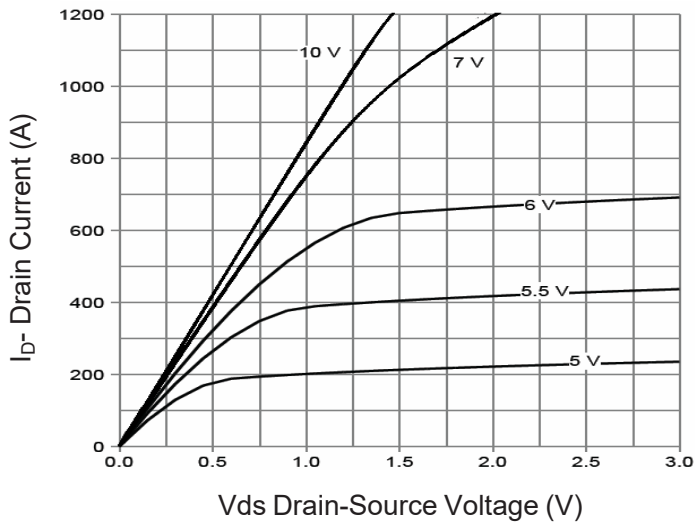


Figure 1 Output Characteristics

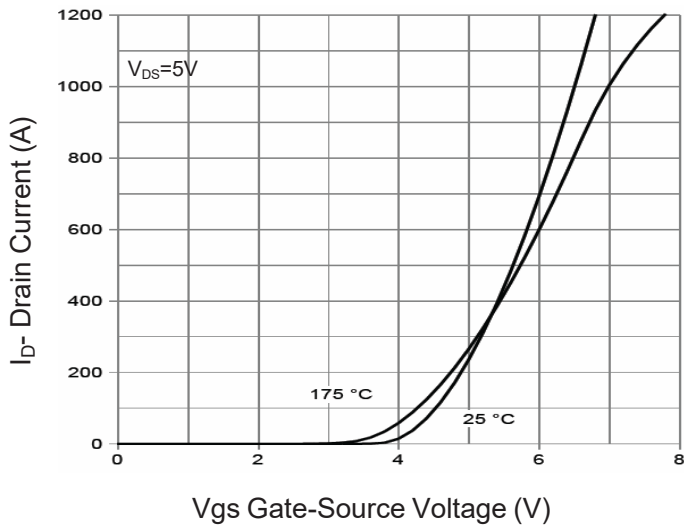


Figure 2 Transfer Characteristics

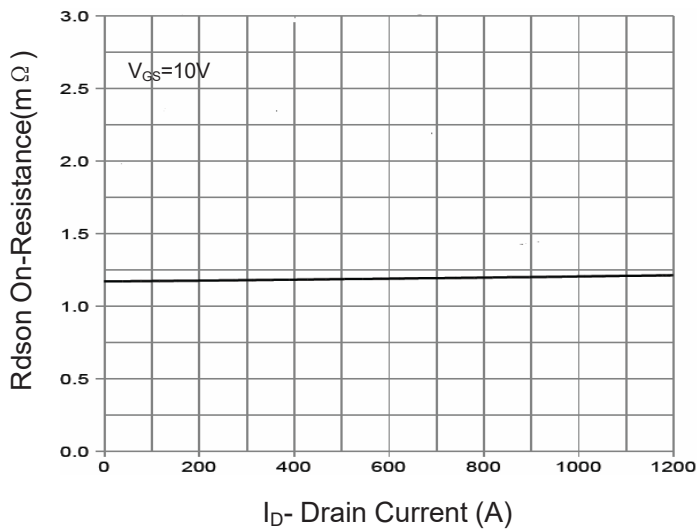


Figure 3 Rdson- Drain Current

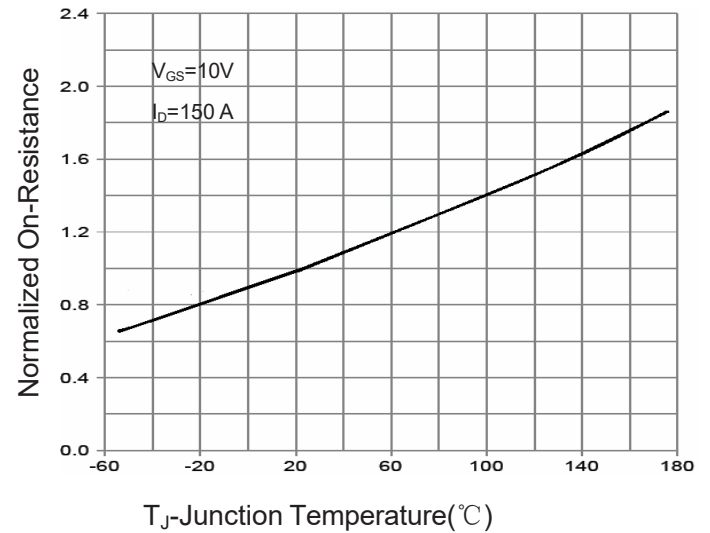


Figure 4 Rdson-Junction Temperature

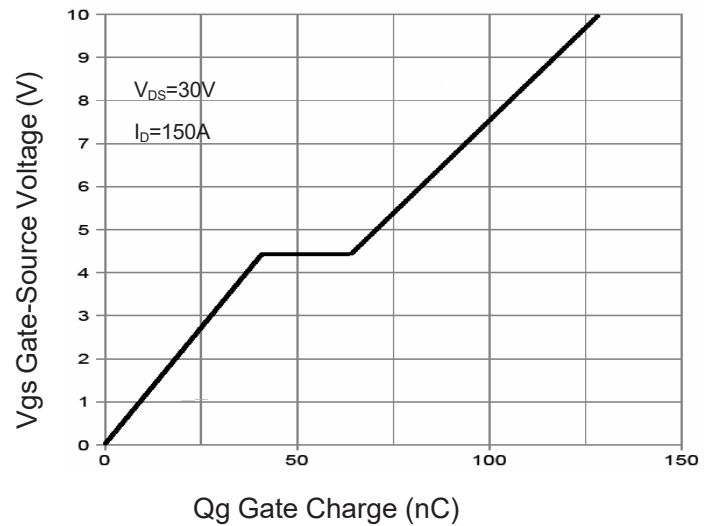


Figure 5 Gate Charge

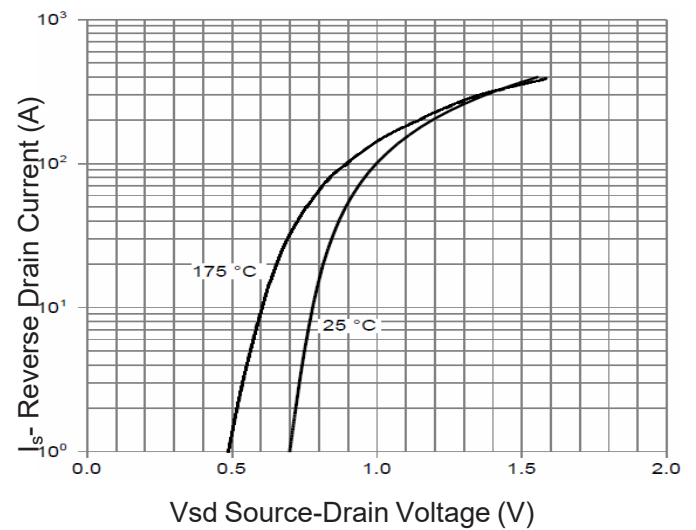
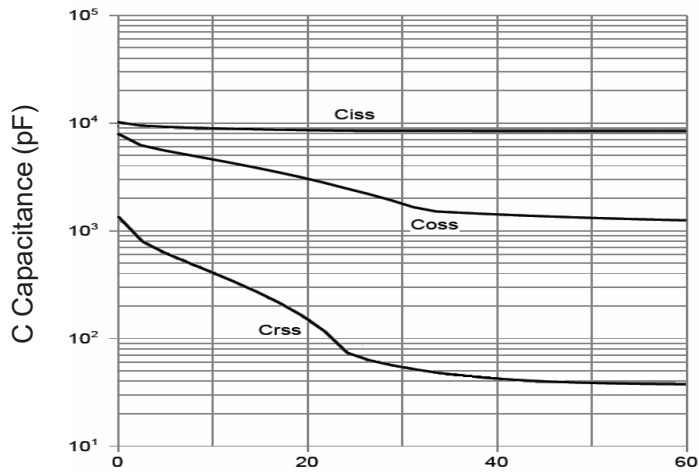
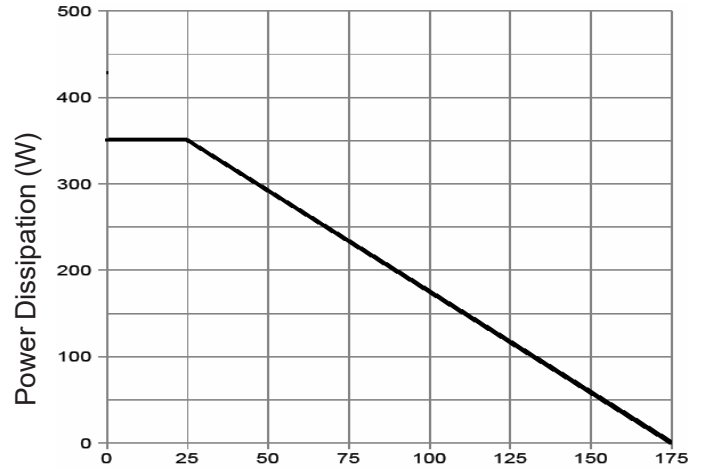


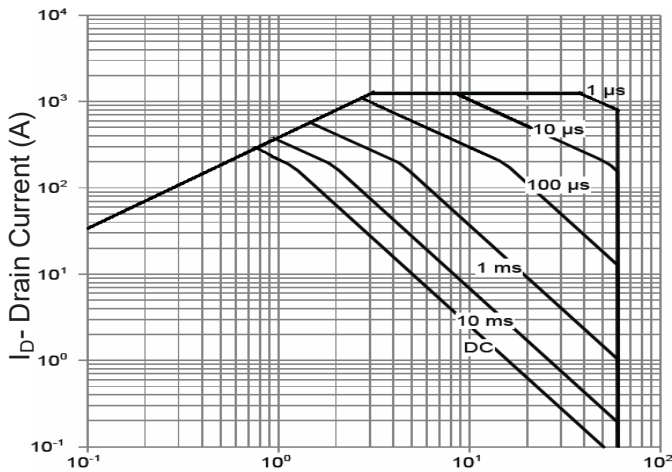
Figure 6 Source- Drain Diode Forward



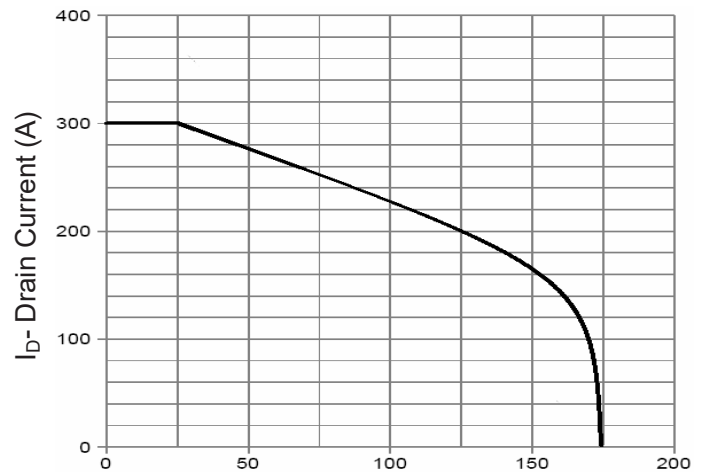
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



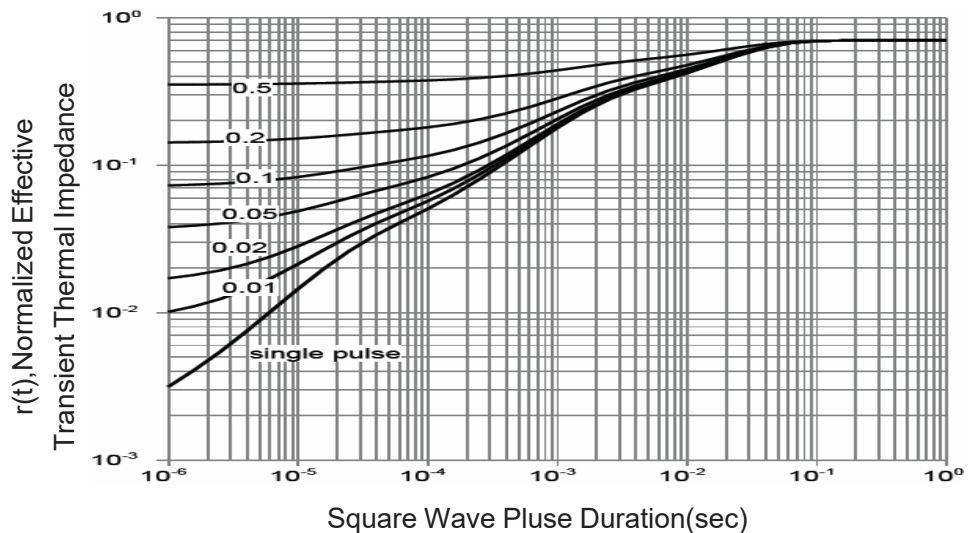
TJ-Junction Temperature(°C)
Figure 9 Power De-rating



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



TJ-Junction Temperature (°C)
Figure 10 Current De-rating



Square Wave Pluse Duration(sec)
Figure 11 Normalized Maximum Transient Thermal Impedance